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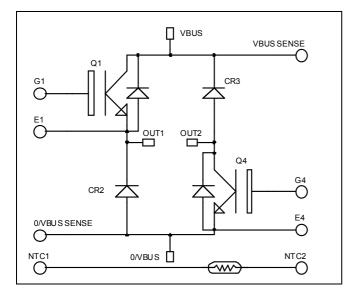
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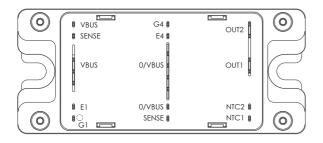
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Asymmetrical - Bridge Fast Trench + Field Stop IGBT3 Power Module





Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage		1200	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	140	
$\begin{tabular}{c c c c c c c } \hline V_{CES} & Colle \\ \hline I_C & Cont \\ \hline I_{CM} & Pulse \\ \hline V_{GE} & Gate \\ \hline P_D & Maxi \\ \hline \end{tabular}$	Continuous Conector Current	$T_C = 80^{\circ}C$	100	А
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	200	
V_{GE}	Gate – Emitter Voltage		±20	V
PD	Maximum Power Dissipation	$T_C = 25^{\circ}C$	480	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	200A @ 1100V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

APTGT100DH120TG

$V_{CES} = 1200V$ $I_{C} = 100A$ @ Tc = 80°C

Application

- Welding converters
- Switched Mode Power Supplies
- Switched Reluctance Motor Drives

Features

- Fast Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
 - Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
 - High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- Low profile
- RoHS Compliant



All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				250	μΑ
V	Collector Emitter Saturation Voltage	OE 10	$T_j = 25^{\circ}C$	1.4	1.7	2.1	V
V _{CE(sat)}			$T_j = 125^{\circ}C$		2.0		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 2 \text{ mA}$		5.0	5.8	6.5	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$			7200		
Coes	Output Capacitance				400		pF
C _{res}	Reverse Transfer Capacitance				300		
T _{d(on)}	Turn-on Delay Time	Inductive Switching	g (25°C)		260		
Tr	Rise Time	$V_{GE} = \pm 15V$			30		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 600V$ $I_C = 100A$			420		ns
$T_{\rm f}$	Fall Time	$R_G = 3.9\Omega$		70			
T _{d(on)}	Turn-on Delay Time	Inductive Switching	g(125°C)		290		
Tr	Rise Time	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 100A$			50		
T _{d(off)}	Turn-off Delay Time				520		ns
$T_{\rm f}$	Fall Time	$R_G = 3.9\Omega$			90		
Eon	Turn on Energy	$\mathbf{v}_{\text{Bus}} = 600 \mathbf{v}$	= 125°C		10		mJ
E _{off}	Turn off Energy	$\begin{array}{c} I_{C} = 100A \\ R_{G} = 3.9\Omega \end{array} \qquad T_{j}$	= 125°C		10		1115

Diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I _{RM}	Maximum Reverse Leakage Current	V _R =1200V	$T_{i} = 25^{\circ}C$ $T_{i} = 125^{\circ}C$			250 500	μΑ
I _F	DC Forward Current		$Tc = 80^{\circ}C$		100		А
V _F	Diode Forward Voltage	$I_{\rm F} = 100 {\rm A}$	$T_i = 25^{\circ}C$		1.4	2.1	V
▼ F	Diode Porward Voltage	$V_{GE} = 0V$	$T_{i} = 125^{\circ}C$		1.3		v
t _{rr}	Reverse Recovery Time	$T_{j} = 25^{\circ}C$ $T_{j} = 125^{\circ}C$	$T_j = 25^{\circ}C$		150		ns
۹rr			$T_{j} = 125^{\circ}C$		250		
0	Reverse Recovery Charge	$I_{\rm F} = 100 \text{A}$ $V_{\rm R} = 600 \text{V}$ $di/dt = 2500 \text{A}/\mu \text{s}$	$T_j = 25^{\circ}C$		10		uС
Q _{rr}	Reverse Recovery Charge		$T_{i} = 125^{\circ}C$		19		μC
Б	Reverse Recovery Energy	-	$T_j = 25^{\circ}C$		4.5		mI
Er			$T_{j} = 125^{\circ}C$		8		mJ

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2 - 6



Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K
-	D				

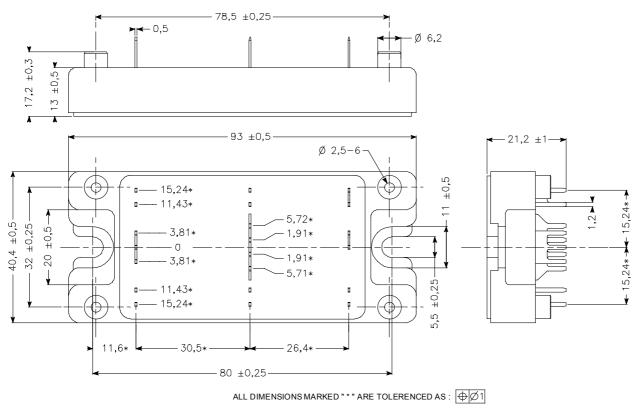
$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]} \quad \text{T: Then } R_{T}: \text{ Then } R_{T}: R_$$

Thermistor temperature : Thermistor value at T

Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance	IGBT			0.26	°C/W	
		Diode			0.34	C/ W	
VISOL	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
TJ	Operating junction temperature range			-40		150	
T _{STG}	Storage Temperature Range		-40		125	°C	
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight					160	g

SP4 Package outline (dimensions in mm)



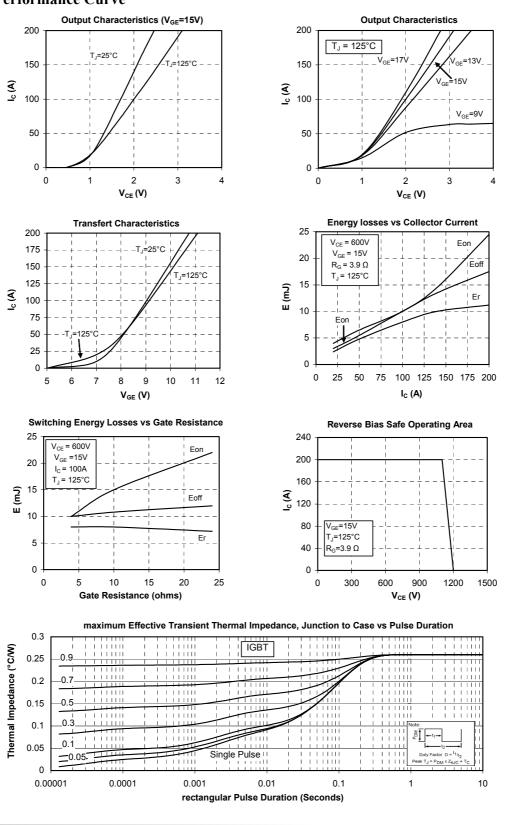
See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

APTGT100DH120TG-Rev 3 October, 2012



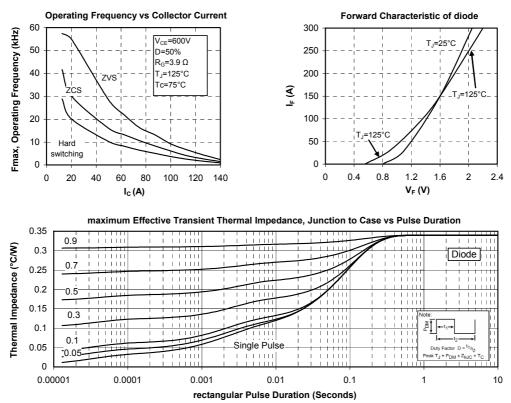
Typical Performance Curve

APTGT100DH120TG



APTGT100DH120TG-Rev 3 October, 2012







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